1 &KDQQHO (QKDQFHPHQW 0RGH)LHOG (

3URGXFW 6XPPDU\

- V_{DS} 60V
- I_D 150A
- $R_{DS(ON)}$(at V_{GS}= 10V) 5.5mohm
- 100% UIS Tested
- 100% V_{DS} Tested

*HQHUDO 'HVFULSWLRQ

- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Part no. with suffix “Q” means AEC-Q101 qualified

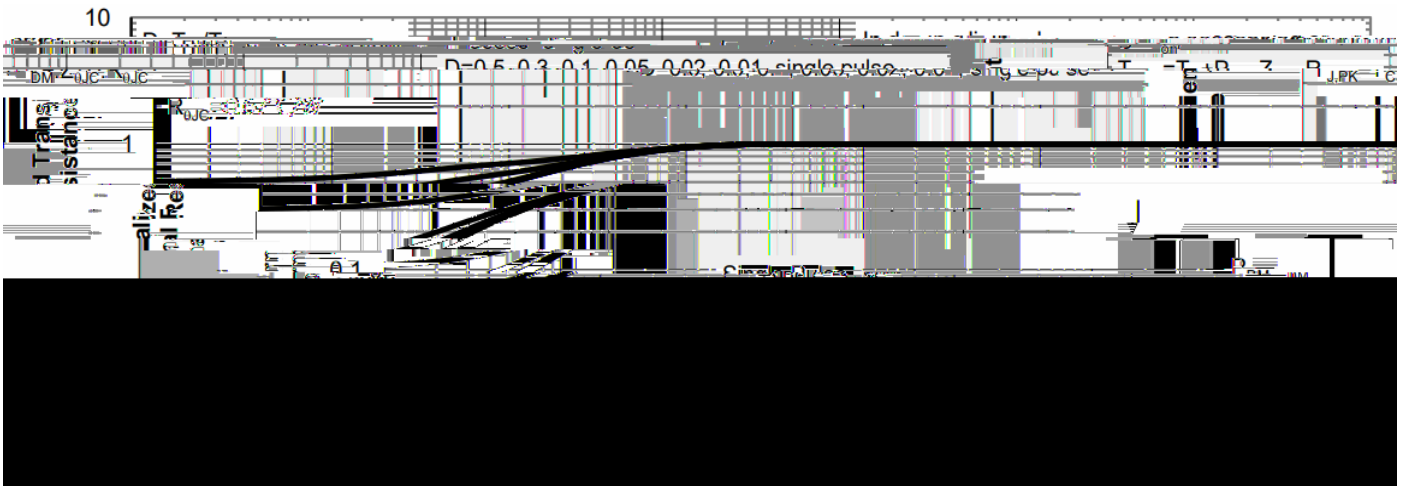
YJB150N06BQ	F2	Y

Pulsed Drain Current [A]			
Total Power Dissipation	T_C=25		
	T_C=100		
Single Pulse Avalanche Energy			
Thermal Resistance Junction-to-Case [B]			
Junction and Storage Temperature Range			

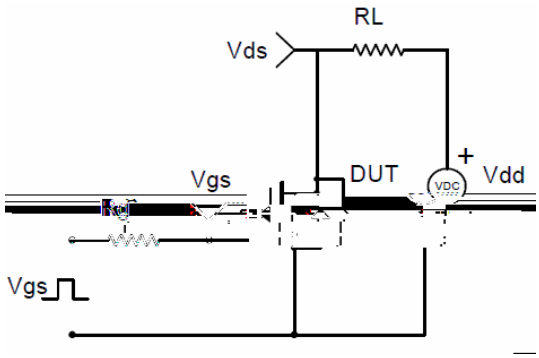
Drain-source Voltage	V_{DS}	60	V

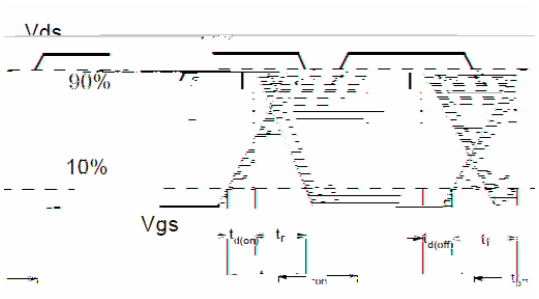
)LJXUH 6DIH 2SHUDWLRQ $UHD

)LJXUH 0D[LPXP &RQWLQXRXV 'UDLQ &XUUHQW YV &DVH 7HPSHUDWXUH

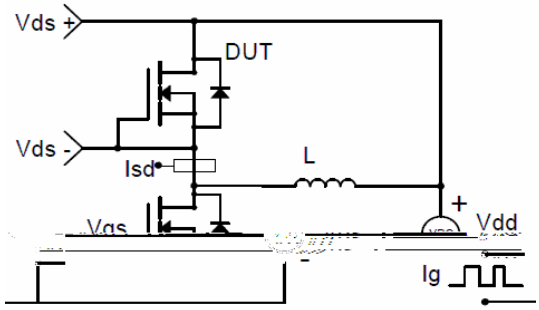


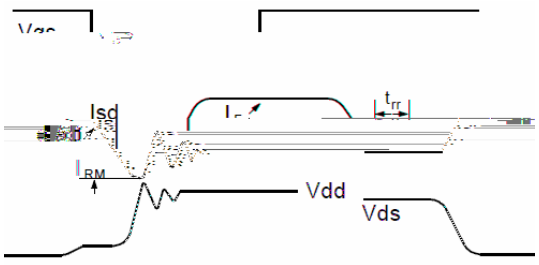
)LJXUH 1RUPDOL]HG 7UDQVLHQW 7KHUPDO ,PSHGDQFH



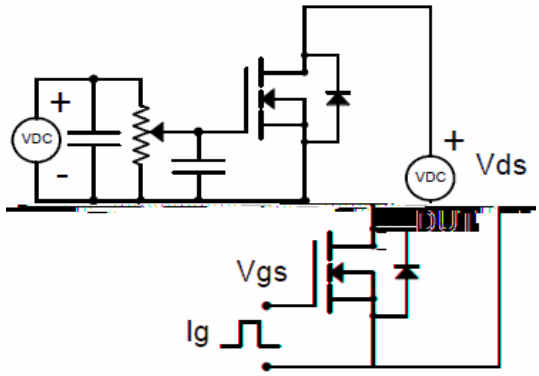


5 H V L V W L Y H 6 Z L W F K L Q J 7 H V W & L U F X L W :D Y H I R U P V

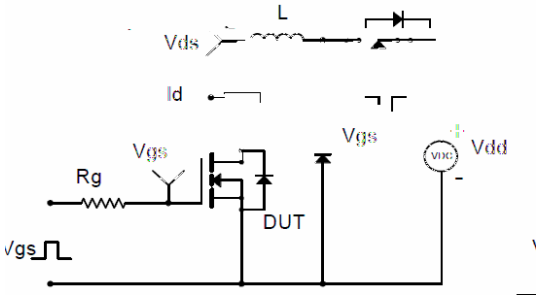




'L R G H 5 H F R Y H U \ 7 H V W & L U F X L W :D Y H I R U P V



*D W H & K D U J H 7 H V W & L U F X L W :D Y H I R U P



8 Q F O D P S H G , Q G X F W L Y H 6 Z L W F K L Q J 8 , 6 7 H V W & L U F X L W